

ABSTRACT OF THE DISCLOSURE

Within both a field effect transistor (FET) device and a method for fabricating the field effect transistor (FET) device there is provided: (1) a semiconductor substrate; (2) a gate electrode formed over the semiconductor substrate and covering a channel region within the semiconductor substrate; and (3) a pair of source/drain regions formed within the semiconductor substrate and separated by the channel region within the semiconductor substrate. Within both the field effect transistor (FET) device and the method for fabricating the field effect transistor (FET) device, at least one of: (1) an interface of the channel region covered by the gate electrode; and (2) an upper surface of the gate electrode, is corrugated.